

Serial No.:

Inventor(s): Farnworth et al.

A3
concl
b) applying force sufficient to cause said one raised portion to penetrate its respective contact location on the die, but less than a force which would cause portions of the contacts outside of the raised portion to substantially penetrate said contact location. *h*

REMARKS


This continuation application claims the feature of contacts being formed so as to extend sufficiently that it is self-limiting, thereby preventing excessive penetration of the bondpad region of a semiconductor die. Therefore, penetration of an oxide layer or surface of a bondpad may be more reliably controlled so as to minimize bondpad damage.

The original disclosure describes this on page 9, lines 7-15, and on page 17, line 19 through page 18, line 15, which refer to the feature as shown in Figure 6. Accordingly, no new matter is presented by the new claims.

It is submitted that the application is in a condition for allowance. Such allowance at an early date is respectfully requested.

If the Examiner feels that a conference will expedite the prosecution of this case, the Examiner is cordially invited to call the undersigned. To that end, an Examiner's amendment to this case would be welcomed and appreciated.

Respectfully submitted,



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SP/dd